



SOITEC AND INTELLIEPI ENTER IN COLLABORATION AGREEMENT TO BETTER SERVE THE GALLIUM ARSENIDE (GaAs) MARKET

Bernin (Grenoble), France, and Richardson, Texas, December 12, 2013 — Soitec (Euronext), a world leader in generating and manufacturing revolutionary semiconductor materials for the electronics and energy industries, and Intelligent Epitaxy Technology, Inc. (IntelliEPI, GTSM Taiwan: F-IET 4971), a leader in providing indium phosphide (InP), gallium arsenide (GaAs), and gallium antimonide (GaSb) epitaxial wafers to the electronics and optoelectronics industries, have signed a collaborative agreement to better serve the GaAs market.

This partnership aims at addressing the market requirements for a reliable second source, while also extending the leadership position of both companies in the GaAs market as well as delivering the best product at the lowest cost for the customers. The agreement includes a technology license granted by Soitec to IntelliEPI, which may be extended to address future business opportunities in the GaAs market, including equipment transfer.

"We are delighted to announce the license of our technology leading to a second source for our products for our key GaAs customers," said Bernard Aspar, Senior Vice President and Soitec's Communication & Power Business Unit General Manager.

"This collaborative agreement will reinforce our GaAs technology and product know-how while, at the same time, offering Soitec's customers supply-chain security," said Yung-Chung Kao, IntelliEPI President and CEO.

Gallium arsenide (GaAs) is a compound of the elements gallium and arsenic. It is a III-V semiconductor, and is used in the manufacture of devices such as microwave frequency integrated circuits, monolithic microwave integrated circuits, infrared light-emitting diodes, laser diodes, solar cells and optical windows. GaAs is often used as a substrate material for the epitaxial growth of other III-V semiconductors including InGaAs and GaInNAs.

About IntelliEPI: Intelligent Epitaxy Technology, Inc. (IntelliEPI) was established in 1999 in Richardson, Texas, to supply epitaxy-based compound semiconductor epi wafers to the electronics and optoelectronics industries. The company utilizes its proprietary real-time in situ growth monitoring technology on molecular beam epitaxy (MBE) systems for the manufacturing of epi wafers on GaAs and InP substrates. Along with IntelliEPI's extensive experience in MBE processing, the company owns three U.S. patents on real-time in situ growth sensor technology. For more information, visit: www.intelliepi.com.

Investor Relations –US George Wang 972-234-0068 x 106 **investors@intelliepi.com** Investor Relations-Taiwan Orson Fan (02) 2514-0582 info@intelliepi.com About Soitec: Soitec is an international manufacturing company, a world leader in generating and manufacturing revolutionary semiconductor materials at the frontier of the most exciting energy and electronic challenges. Soitec's products include substrates for microelectronics (most notably SOI: Silicon-on-Insulator) and concentrator photovoltaic systems (CPV). The company's core technologies are Smart CutTM, Smart StackingTM and ConcentrixTM, as well as expertise in epitaxy. Applications include consumer and mobile electronics, microelectronics-driven IT, telecommunications, automotive electronics, lighting products and large-scale solar power plants. Soitec has manufacturing plants and R&D centers in France, Singapore, Germany and the United States. For more information, visit: www.soitec.com.

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